

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A) ^d	Q_g (Typ.)
- 20	0.039 at $V_{GS} = - 4.5$ V	- 5.3	13.6 nC
	0.050 at $V_{GS} = - 2.5$ V	- 4.7	
	0.075 at $V_{GS} = - 1.8$ V	- 3.8	

FEATURES

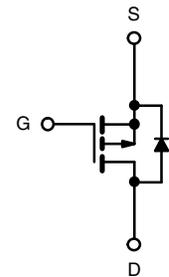
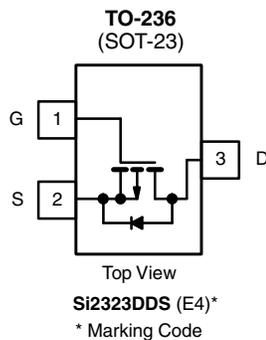
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch
- PA Switch
- DC/DC Converters
- Power Management



P-Channel MOSFET

Ordering Information:
Si2323DDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	- 20	V	
Gate-Source Voltage	V_{GS}	± 8		
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	- 5.3	A	
	$T_C = 70$ °C	- 4.3		
	$T_A = 25$ °C	- 4.1 ^{a,b}		
	$T_A = 70$ °C	- 3.2 ^{a,b}		
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	- 20		
Continuous Source-Drain Diode Current	$T_C = 25$ °C	- 1.4		
	$T_A = 25$ °C	- 0.8 ^{a,b}		
Maximum Power Dissipation	$T_C = 25$ °C	1.7	W	
	$T_C = 70$ °C	1.1		
	$T_A = 25$ °C	0.96 ^{a,b}		
	$T_A = 70$ °C	0.62 ^{a,b}		
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	$t \leq 5$ s	R_{thJA}	100	130	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	60	75	

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 175 °C/W.
- $T_C = 25$ °C.

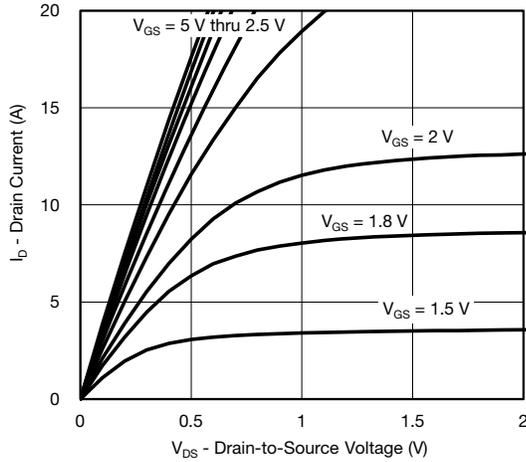
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-13		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-2.8		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.4		-1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -4.1\text{ A}$		0.032	0.039	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2\text{ A}$		0.041	0.050	
		$V_{GS} = -1.8\text{ V}, I_D = -1\text{ A}$		0.058	0.075	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -4.1\text{ A}$		18		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1160		pF
Output Capacitance	C_{oss}			135		
Reverse Transfer Capacitance	C_{rss}			120		
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -8\text{ V}, I_D = -4.1\text{ A}$		24	36	nC
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4.1\text{ A}$		13.6	21	
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			2.2		
Gate Resistance	R_g	$f = 1\text{ MHz}$	2	10	20	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 3.1\text{ }\Omega$ $I_D \cong -3.2\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		24	36	ns
Rise Time	t_r			22	40	
Turn-Off Delay Time	$t_{d(off)}$			52	78	
Fall Time	t_f			11	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 3.1\text{ }\Omega$ $I_D \cong -3.2\text{ A}, V_{GEN} = -8\text{ V}, R_g = 1\text{ }\Omega$		8	16	
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			58	87	
Fall Time	t_f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-1.4	A
Pulse Diode Forward Current	I_{SM}				-20	
Body Diode Voltage	V_{SD}	$I_S = -3.2\text{ A}, V_{GS} = 0\text{ V}$		-0.79	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		14	25	ns
Body Diode Reverse Recovery Charge	Q_{rr}			6	12	nC
Reverse Recovery Fall Time	t_a			8		ns
Reverse Recovery Rise Time	t_b			6		

Notes:

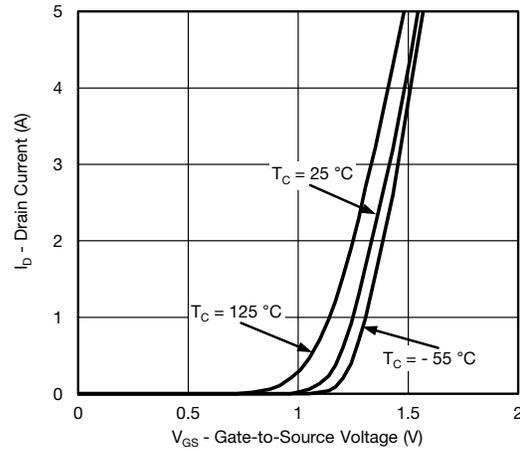
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

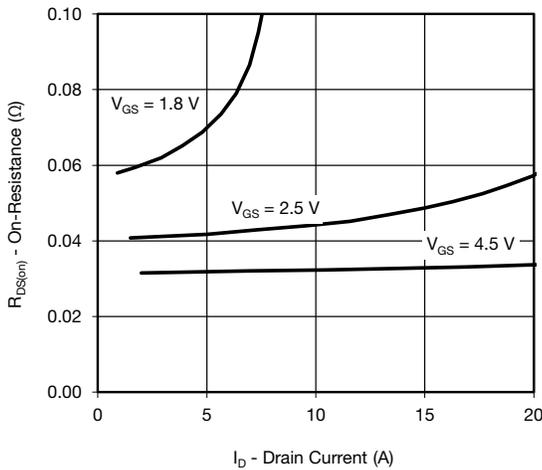
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



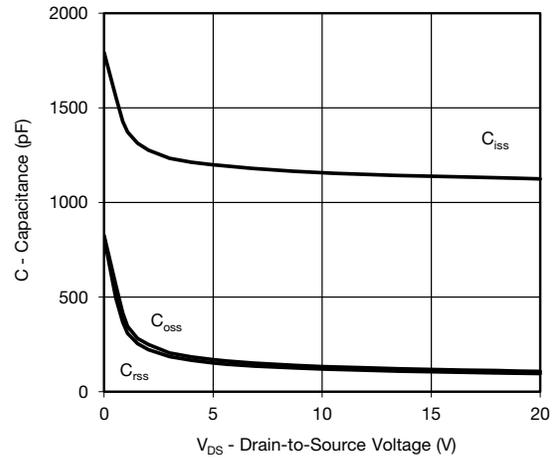
Output Characteristics



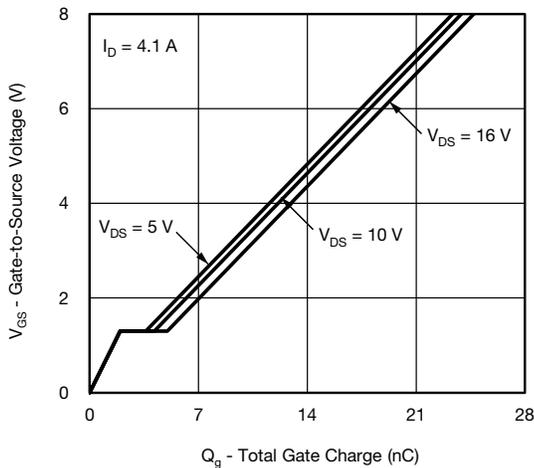
Transfer Characteristics



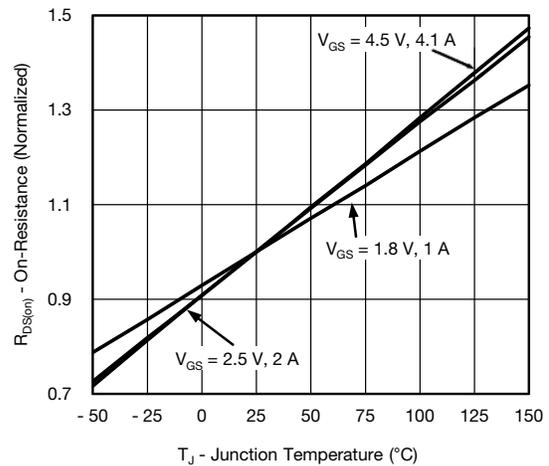
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

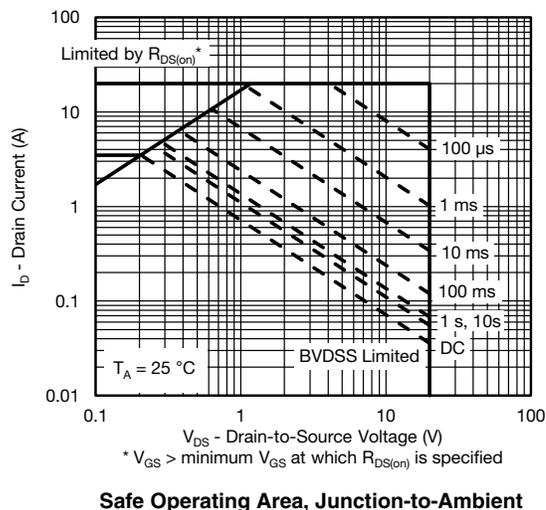
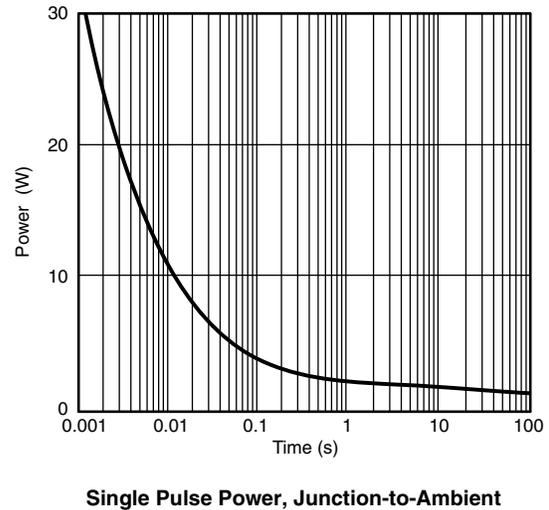
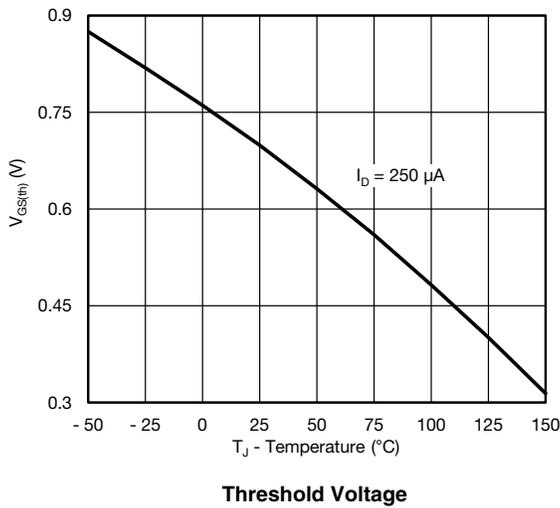
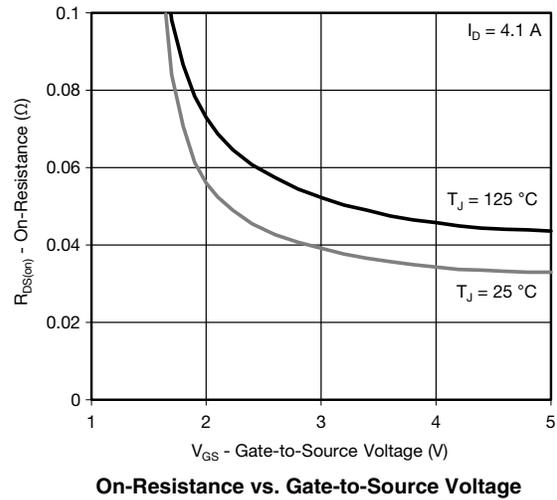
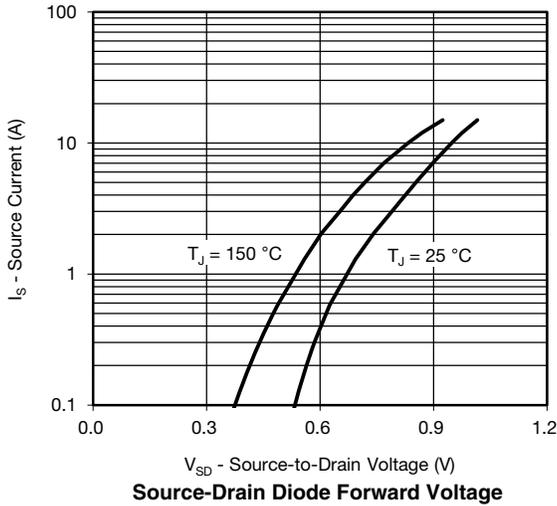


Gate Charge

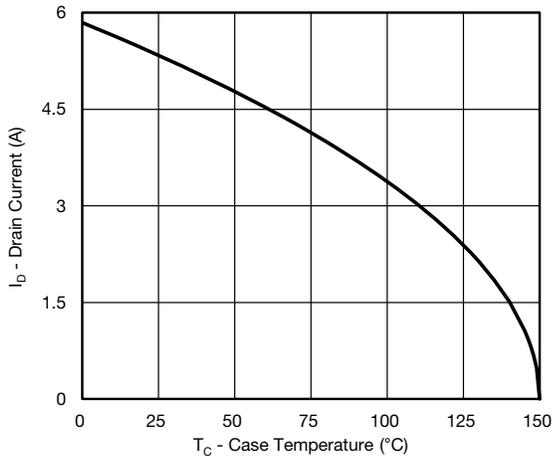


On-Resistance vs. Junction Temperature

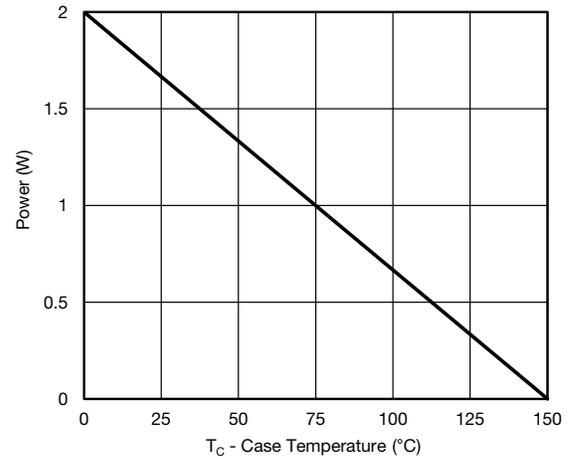
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



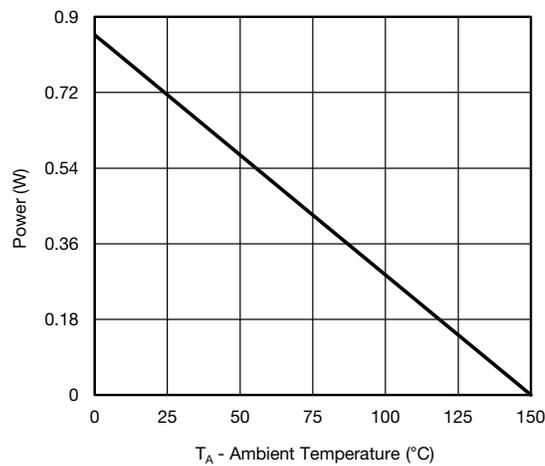
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



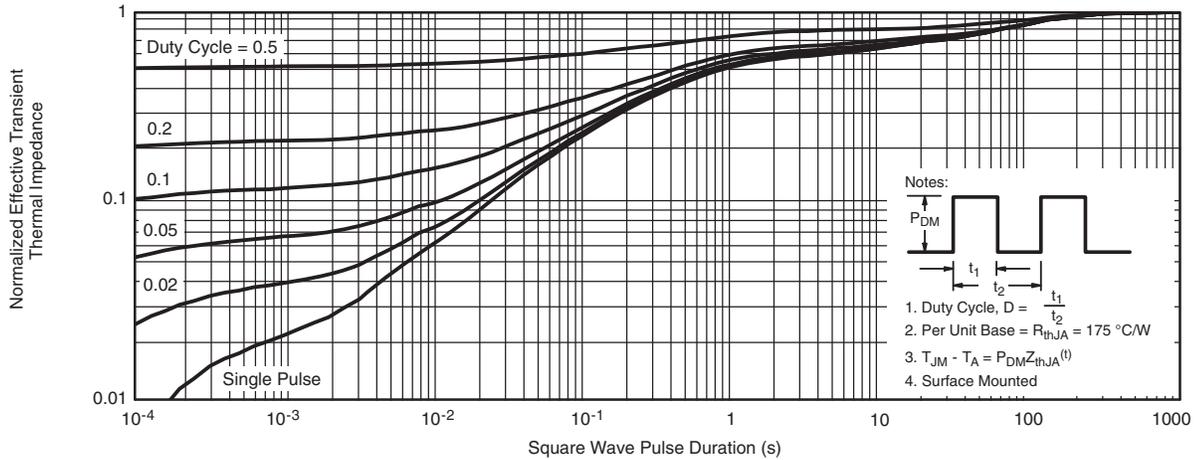
Power Derating, Junction-to-Foot



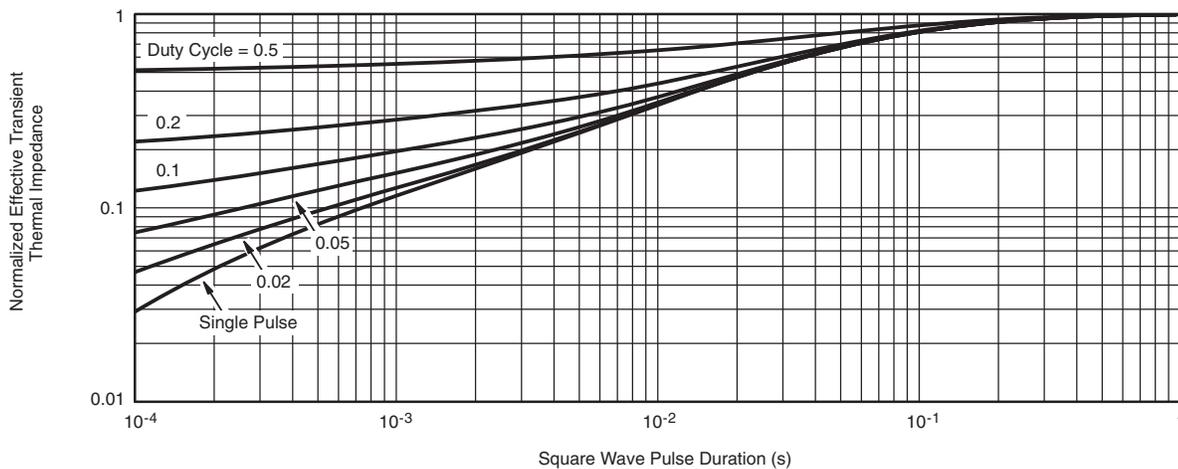
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



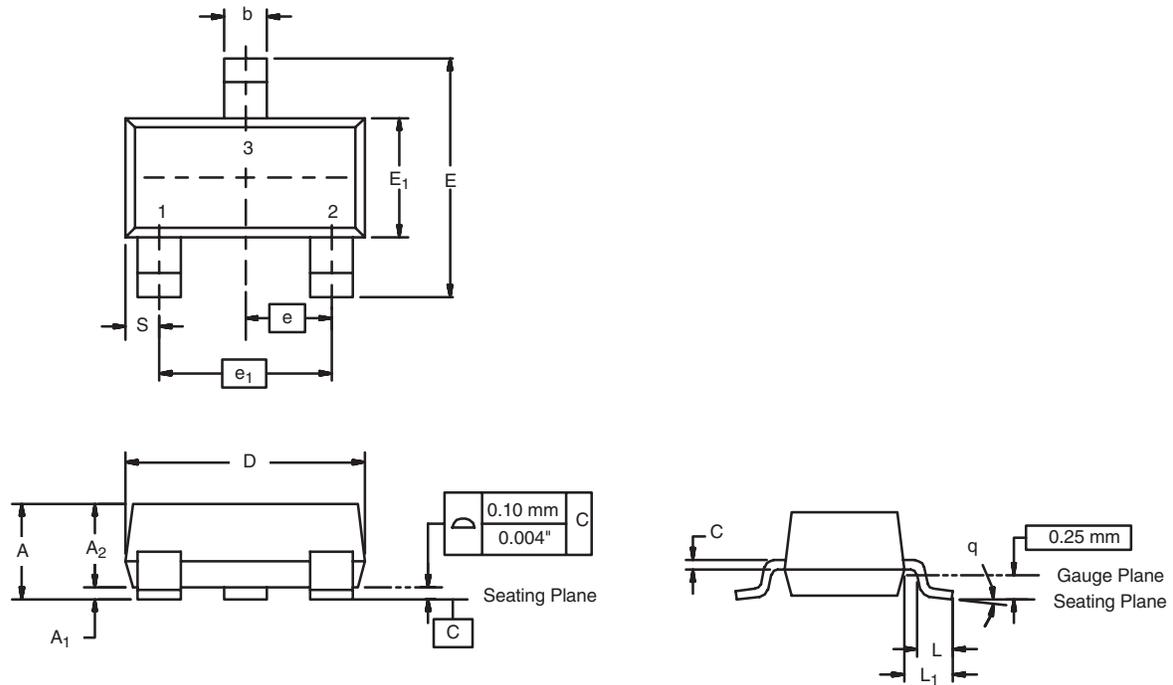
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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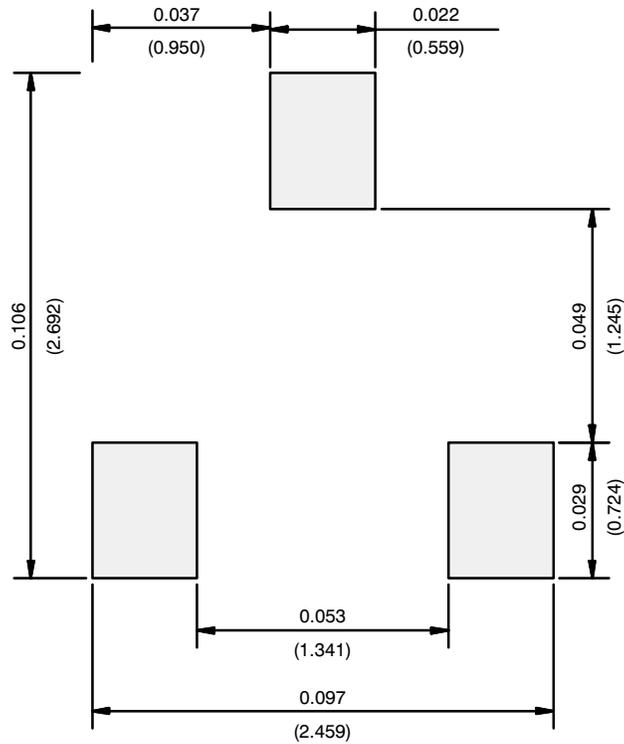
SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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